

MMG200D120UA6TC

IGBT

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit		
V _{GE(th)}	Gate Emitter Threshold Voltage	5.0	5.8	6.5			
V _{CE(sat)}	Collector - Emitter Saturation Voltage						
		I _C =20	G _E =15	J=25	1.8	2.25	V
		I _C =20	G _E =15	J=12	2.1		
	I _C =20	G _E =15	J=15	2.15			
I					nA		
					μC		
					nF		
					pF		
					ns		
					ns		
					ns		
					ns		
					ns		
					ns		
					ns		
					ns		
					ns		
					ns		
					ns		
					mJ		
					mJ		
					mJ		
					mJ		
					K /W		
					Unit		
					ns		
					A		
					μC		
					mJ		
					K /W		

T_{Jop}

Unit

V

Nm

Nm

g

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$I_F(A)$

$V_F(V)$

Figure 9. Diode Forward Characteristics Diode

$E_{REC}(mJ)$

$R_{g\ddot{A}} \text{ \AA}$

Figure 10. Switching Energy vs Gate Resistor Diode

$E_{REC}(mJ)$

$I_F A$

$Z_{th_{jc}}(K/W)$

